- **Diode-pumped solid state laser with 355 nm wavelength**
  - **Exposure of standard i-line resists**
- **Automatic handling of 150 mm wafers and 6“ masks**
- **Exposure of substrates with almost arbitrary form factor with manual handling (max. thickness 9 mm)**
- **Maximum exposure area 400 mm x 400 mm**
- **Front to backside alignment possible**
- **3 exchangeable write heads with different resolution and throughput**
- **Exposure of high topography substrates with special write head with increased working distance**
- **Greyscale lithography**

Parameter	Write Mode I	Write Mode II	Write Mode III
Focal Length	4 mm	10 mm	20 mm
Min. Feature Size	700 nm	1000 nm	2000 nm
CD Uniformity	65 nm	75 nm	110 nm
Edge Roughness	40 nm	50 nm	70 nm
Overlay Accuracy	200 nm	350 nm	500 nm
Write Speed @ 50mJ/cm^2	205 mm^2/min	1200 mm^2/min	4200 mm^2/min
Adress grid	10 nm	25 nm	50 nm

- **Exposure time is independent from specific form or complexity of pattern**

Throughput

- Up to some max. value, it is also independent from dose
- Write time for exposures on 1µm i-line resist :

Patterned area	Write Mode I	Write Mode II	Write Mode III
150 mm wafer	1h52min	0h22min	0h11min
200 mm wafer	3h13min	0h36min	0h18min
300 mm wafer	7h02min	1h16min	0h38min
6 inch mask	1h52min	0h22min	0h11min
9 inch mask	4h13min	0h46min	0h23min